

系所組別： 電機工程學系甲組

考試科目： 電子材料概論

考試日期： 0307 · 節次： 2

※ 考生請注意：本試題 可 不可 使用計算機

1. Iron at 20°C is BCC with atoms of atomic radius 0.124nm . Calculate the lattice constant a for the cube edge of the iron unit cell . (20%)
2. Copper has an FCC crystal structure and an atomic radius of 0.1278nm . Assuming the atoms to be hard spheres that touch each other along the face diagonals of the FCC unit cell. Calculate a theoretical value for the density of copper. The atomic mass of copper is 63.54 g/mol . (20%)
3. Fig.(1) shows a hypothetical binary eutectic phase diagram on which we indicate an alloy of composition 0.27B . Calculate the following quantities (20%)
 - a. The fraction of primary solid that forms under equilibrium cooling at the eutectic temperature .
 - b. The fraction of liquid with the eutectic composition that will transform to two solid phases below the eutectic isotherm
 - c. The amount of α and β that will form from the liquid just below the eutectic isotherm.
 - d. The total amount of phase in the alloy at a temperature just below the eutectic temperature.
4. Please address the effect of temperature and impurity on the conductivity for metal, insulator and semiconductor, respectively.(20%)
5. Calculate the electrical resistivity of intrinsic silicon at 300K . For Si at 300 K $n_i=1.5\times 10^{16}$ carriers/ m^3 , $q=1.6\times 10^{-19}\text{C}$, $\mu_n=0.135\text{m}^2/\text{V}\cdot\text{s}$, and $\mu_p=0.038\text{m}^2/\text{V}\cdot\text{s}$, and (20%)

Fig.(1)

